

L Number	Hits	Search Text	DB	Time stamp
15	0	esd and (over adj voltage) and (first adj buried adj layer) and (first adj base)	USPAT; US-PGPUB	2002/11/20 10:24
16	0	(esd or (over adj voltage)) and (first adj buried adj layer) and (first adj base)	USPAT; US-PGPUB	2002/11/20 10:26
17	12	(first adj buried adj layer) and (first adj base)	USPAT; US-PGPUB	2002/11/20 10:33
18	5	semiconductor adj device adj both adj surfaces	USPAT; US-PGPUB	2002/11/20 10:35
19	22	double adj bipolar	USPAT; US-PGPUB	2002/11/20 10:37
20	2311	double adj (heterostructure or heterojunction)	USPAT; US-PGPUB	2002/11/20 11:05
21	1	two adj terminal adj surge adj protection	USPAT; US-PGPUB	2002/11/20 11:07
22	0	double adj terminal adj surge adj protection	USPAT; US-PGPUB	2002/11/20 11:08
23	0	plural adj terminal adj surge adj protection	USPAT; US-PGPUB	2002/11/20 11:08
24	122	(two adj terminal) and (surge adj protection)	USPAT; US-PGPUB	2002/11/20 11:14
26	12	two adj terminal adj semiconductor adj devices	USPAT; US-PGPUB	2002/11/20 11:16
27	12	two adj terminal adj bipolar	USPAT; US-PGPUB	2002/11/20 11:26
28	192	(two adj terminal) and (first adj base)	USPAT; US-PGPUB	2002/11/20 13:21
29	206	first adj buried adj layer	USPAT; US-PGPUB	2002/11/20 13:41
30	265	surge adj protection adj device	USPAT; US-PGPUB	2002/11/20 15:07
31	2	ring adj shaped adj moats	USPAT; US-PGPUB	2002/11/20 15:19
32	88	isolation adj moat	USPAT; US-PGPUB	2002/11/20 16:02
33	0	4292646.pn. and oxide	USPAT; US-PGPUB	2002/11/20 17:01
34	1	5962878.pn. and exposed	USPAT; US-PGPUB	2002/11/20 17:02
35	1	5962878.pn. and diffusing	USPAT; US-PGPUB	2002/11/20 17:02